

TSMC-01-796/786



March 5, 2002

Encl T746
3
BT
4-11-02

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

RECEIVED
MAR 29 2002
TC 1700

Subject:

Serial No. 10/042,573 01/09/02

Kei-Wei Chen

REMOVAL OF SION RESIDUE AFTER

Grp. Art Unit: 1746

RECEIVED
APR 4 2002
TC 1700 MAIL ROOM

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.


The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner of Patents and
Trademarks, Washington, D.C. 20231, on March 15, 2002.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 3/15/02

U.S. Patent 5,704,987 to Huynh et al., "Process for Removing Residue from a Semiconductor Wafer After Chemical-Mechanical Polishing," discloses a post CMP clean using TMAH (tetramethyl ammonium hydroxide).

U.S. Patent 6,194,366 to Naghshineh et al., "Post Chemical-Mechanical Planarization (CMP) Cleaning Composition," discloses a post CMP clean comprising TMAH.

The following two U.S. Patents discloses a post CMP clean that uses TMAH:

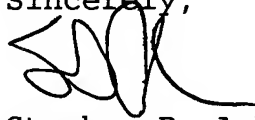
- 1) U.S. Patent 6,152,148 to George et al., "Method for Cleaning Semiconductor Wafers Containing Dielectric Films."
- 2) U.S. Patent 6,099,662 to Wang et al., "Process for Cleaning a Semiconductor Substrate After Chemical-Mechanical Polishing."

The following six U.S. Patents describe Post CMP clean comprising TMAH:

- 1) U.S. Patent 5,981,454 to Small, "Post Clean Treatment Composition Comprising an Organic Acid and Hydroxylamine."

- 2) U.S. Patent 6,044,851 to Grieger et al., "Cleaning Composition Containing Tetraalkylammonium Salt and Use Thereof in Semiconductor Fabrication."
- 3) U.S. Patent 6,235,145 to Li et al., "System for Wafer Cleaning."
- 4) U.S. Patent 6,046,112 to Wang, "Chemical Mechanical Polishing Slurry."
- 5) U.S. Patent 6,114,241 to Choi et al., "Method of Manufacturing a Semiconductor Device Capable of Reducing Contact Resistance."
- 6) U.S. Patent 5,679,169 to Gonzales et al., "Method for Post Chemical-Mechanical Planarization Cleaning of Semiconductor Wafers."

Sincerely,



Stephen B. Ackerman,
Reg. No. 37761